LECTURE 140 – THE MOS SWITCH AND MOS DIODE

LECTURE ORGANIZATION

Outline
- MOSFET as a switch
- Influence of the switch resistance
- Influence of the switch capacitors
  - Channel injection
  - Clock feedthrough
- Using switches at reduced values of $V_{DD}$
- MOS Diode
- Summary

CMOS Analog Circuit Design, 2nd Edition Reference
Pages 113-124

Switch Model
- An ideal switch is a short-circuit when ON and an open-circuit when OFF. $V_C =$ controlling terminal for the switch ($V_C$ high ⇒ switch ON, $V_C$ low ⇒ switch OFF)

- Actual switch:
  $r_{on}$ = resistance of the switch when ON
  $r_{off}$ = resistance of the switch when OFF
  $V_{OS}$ = offset voltage when the switch is ON
  $I_{off}$ = offset current when the switch is OFF
  $I_A$ and $I_B$ are leakage currents to ground
  $C_A$ and $C_B$ are capacitances to ground
  $C_{AC}$ and $C_{BC}$ = parasitic capacitors between the control terminal and switch terminals
MOS Transistor as a Switch

On Characteristics of a MOS Switch
Assume operation in active region ($v_{DS} < v_{GS} - V_T$) and $v_{DS}$ small.

$$i_D = \frac{\mu C_{ox} W}{L} \left[ (v_{GS} - V_T) - \frac{v_{DS}}{2} \right] v_{DS} \approx \frac{\mu C_{ox} W}{L} (v_{GS} - V_T) v_{DS}$$

Thus,

$$R_{ON} \approx \frac{v_{DS}}{i_D} = \frac{v_{DS}}{\mu C_{ox} W} \left( \frac{v_{GS} - V_T}{v_{DS}} \right)$$

OFF Characteristics of a MOS Switch
If $v_{GS} < V_T$, then $i_D = I_{OFF} = 0$ when $v_{DS} \approx 0V$.
If $v_{DS} > 0$, then

$$R_{OFF} \approx \frac{1}{i_D} = \frac{1}{I_{OFF}} \approx \infty$$

MOS Switch Voltage Ranges
If a MOS switch is used to connect two circuits that can have analog signal that vary from 0 to 1V, what must be the value of the bulk and gate voltages for the switch to work properly?

- To insure that the bulk-source and bulk-drain $pn$ junctions are reverse biased, the bulk voltage must be less than the minimum analog signal for a NMOS switch.
- To insure that the switch is on, the gate voltage must be greater than the maximum analog signal plus the threshold for a NMOS switch.

Therefore:

$$V_{Bulk} \leq 0V$$

$$V_{Gate(on)} > 1V + V_T$$

$$V_{Gate(off)} \leq 0V$$

Unfortunately, the large value of reverse bias bulk voltage causes the threshold voltage to increase.
Current-Voltage Characteristics of a NMOS Switch

The following simulated output characteristics correspond to triode operation of the MOSFET.

![Graph showing current-voltage characteristics of a NMOS switch]

SPICE Input File:

```
MOS Switch On Characteristics
M1 1 2 0 0 MNMOS W=1U L=1U
.MODEL MNMOS NMOS VTO=0.7, KP=110U,
+LAMBDA=0.04, GAMMA=0.4 PHI=0.7
VDS 1 0 DC 0.0
VGS 2 0 DC 0.0
VBS 3 0 DC -5.0
.DC VDS -1 1 0.1 VGS 1 5 0.5
.PRINT DC ID(M1)
.PROBE
.END
```

MOS Switch ON Resistance as a Function of Gate-Source Voltage

![Graph showing MOSFET on resistance as a function of gate-source voltage]

SPICE Input File:

```
MOS Switch On Resistance as a f(W/L)
M1 1 2 0 0 MNMOS W=1U L=1U
M2 1 2 0 0 MNMOS W=5U L=1U
M3 1 2 0 0 MNMOS W=10U L=1U
M4 1 2 0 0 MNMOS W=50U L=1U
.MODEL MNMOS NMOS VTO=0.7, KP=110U,
+LAMBDA=0.04, GAMMA=0.4 PHI=0.7
VDS 1 0 DC 0.01V
VGS 2 0 DC 0.0
.VGS 2 0 DC 1.5 0.1
.PRINT DC ID(M1) ID(M2) ID(M3) ID(M4)
.PROBE
.END
```
**Influence of the ON Resistance on MOS Switches**

Finite ON Resistance:

\[
\text{Example}
\]

Initially assume the capacitor is uncharged. If \( V_{\text{Gate(ON)}} \) is 5V and is high for 0.1 \( \mu \)s, find the W/L of the MOSFET switch that will charge a capacitance of 10pF in five time constants.

**Solution**

The time constant must be 100ns/5 = 20ns. Therefore \( R_{\text{ON}} \) must be less than 
\[
\frac{20\text{ns}}{10\text{pF}} = 2\text{k}\Omega.
\]

The ON resistance of the MOSFET (for small \( v_{DS} \)) is
\[
R_{\text{ON}} = \frac{1}{K'W/L(V_{GS}-V_T)} \Rightarrow \frac{W}{L} = \frac{1}{R_{\text{ON}}K'N} \frac{(V_{GS}-V_T)}{2k\Omega \cdot 110\mu\text{A/V}^2 \cdot 4.3} = 1.06
\]

**Comments:**

- It is relatively easy to charge on-chip capacitors with minimum size switches.
- Switch resistance is really not constant during switching and the problem is more complex than above.

---

**Including the Influence of the Varying On Resistance**

Gate-source Constant

\[
g_{\text{ON}}(t) = \frac{K'W}{L} \left[ (v_{GS(t)}-V_T) - 0.5v_{DS(t)} \right]
\]

\[
g_{\text{ON(aver.)}} = \frac{1}{r_{\text{ON(aver.)}}} \approx \frac{g_{\text{ON(0)}} + g_{\text{ON(\infty)}}}{2}
\]

\[
= \frac{K'W}{2L} \left( V_{GS-V_T} \right) - \frac{K'Wv_{DS(0)}}{4L} + \frac{K'W}{2L} \left( V_{GS-V_T} \right)
\]

\[
= \frac{K'W}{L} \left( V_{GS-V_T} \right) - \frac{K'Wv_{DS(0)}}{4L}
\]

Gate-source Varying

\[
g_{\text{ON}} = \frac{K'W}{2L} \left[ V_{GS(0)}-V_T \right] - \frac{K'Wv_{DS(0)}}{4L} + \frac{K'W}{2L} \left[ V_{GS(\infty)}-V_{IN}-V_T \right]
\]
Example 1 - Switch ON Resistance

Assume that at $t = 0$, the gate of the switch shown is taken to 5V. Design the W/L value of the switch to discharge the $C_1$ capacitor to within 1% of its initial charge in 10ns. Use the MOSFET parameters of Table 3.1-2.

Solution

Note that the source of the NMOS is on the right and is always at ground potential so there is no bulk effect as long as the voltage across $C_1$ is positive. The voltage across $C_1$ can be expressed as

$$v_{C1}(t) = 5 \exp\left(-\frac{-t}{R_{ON}C_1}\right)$$

At 10ns, $v_{C1}$ is 5/100 or 0.05V. Therefore,

$$0.05 = 5 \exp\left(-\frac{-10^{-8}}{R_{ON}10^{-11}}\right) = 5 \exp\left(-10^3\right) \Rightarrow \exp(G_{ON}10^3) = 100 \Rightarrow G_{ON} = \frac{\ln(100)}{10^3}$$

$$= 0.0046 \text{S}$$

$$\therefore 0.0046 = \frac{K'W}{L} (V_{GS}-V_T) - \frac{K'WV_{DS}(0)}{4L} = \left(110 \times 10^{-6} \cdot 4.3 \cdot \frac{110 \times 10^{-6} \cdot 5}{4}\right) \frac{W}{L} = 356 \times 10^{-6} \frac{W}{L}$$

Thus, $\frac{W}{L} = \frac{0.0046}{356 \times 10^{-6}} = 13.71 \approx 14$

Influence of the OFF State on MOS Switches

The OFF state influence is primarily in any current that flows from the terminals of the switch to ground.

An example might be:

$$v_{out}(t) = v_{CH} e^{-V(R_{Bulk}C_H)}$$

If $R_{Bulk} \approx 10^9 \Omega$ and $C_H = 10pF$, the time constant is $10^9 \cdot 10^{-11} = 0.01$ seconds
Influence of Parasitic Capacitances

The parasitic capacitors have two influences:

- Parasitics to ground at the switch terminals ($C_{BD}$ and $C_{BS}$) add to the value of the desired capacitors.
  
  This problem is solved by the use of stray-insensitive switched capacitor circuits

- Parasitics from gate to source and drain cause charge injection and clock feedthrough onto or off the desired capacitors.
  
  This problem can be minimized but not eliminated.

Model for studying gate capacitance:

Channel Charge Injection

Consider the simple switch configuration shown:

When the switch is ON, a charge is stored in the channel which is equal to,

$$Q_{ch} = -WLC_{ox}(V_H - v_{in} - V_T)$$

where $V_H$ is the value of the clock waveform when the switch is on ($V_H \approx V_{DD}$)

When the switch turns OFF, this charge is injected into the source and drain terminals as shown.

Assuming the charge splits evenly, then the change of voltage across the capacitor, $C_L$, is

$$\Delta V = \frac{Q_{ch}}{2C_L} = \frac{-WLC_{ox}(V_H - v_{in} - V_T)}{2C_L}$$

The charge injection does not influence $v_{in}$ because it is a voltage source.
**Clock Feedthrough**

In addition to the charge injection, the overlap capacitors of the MOSFET couple the turning off part of the clock to the load capacitor. This is called *clock feedthrough*. The model for this case is given as:

\[ V_{CL} = \left( \frac{C_L}{C_{OL}+C_L} \right) V_S - \left( \frac{C_{OL}}{C_{OL}+C_L} \right) V_T - (V_S + V_T - V_L) \left( \frac{C_{OL}}{C_L} \right) \]

if \( C_{OL} < C_L \).

Therefore the error voltage is,

\[ V_{error} \approx -(V_S + 2V_T - V_L) \left( \frac{C_{OL}}{C_L} \right) = -(v_{in} + 2V_T - V_L) \left( \frac{C_{OL}}{C_L} \right) \]

---

**Modeling the Influence of Charge Injection and Clock Feedthrough**

The influence of charge injection and clock feedthrough on a switch is a complex analysis which is better suited for computer analysis. Here we will attempt to develop an understanding sufficient to show ways of reducing these effects.

To begin the model development, there are two cases of charge injection depending upon the transition rate when the switch turns off.

1.) Slow transition time – the charge in the channel can react instantaneously to changes in the turning-off, gate-source voltage.

2.) Fast transition time – the charge in the channel cannot react fast enough to respond to the changes in the turning-off, gate-source voltage.
**Slow Transition Time**
Consider the following switch circuit:

1.) During the on-to-off transition time from A to B, the charge injection is absorbed by the low impedance source, $v_{in}$.
2.) The switch turns off when the gate voltage is $v_{in} + V_T$ (point B).
3.) From B to C the switch is off but the gate voltage is changing. As a result charge injection occurs to $C_L$.

---

**Fast Transition Time**
For the fast transition time, the rate of transition is faster than the channel time constant so that some of the charge during the region from point A to point B is injected onto $C_L$ even though the transistor switch has not yet turned off.
A Quantized Model of Charge Injection/Clock Feedthrough

Approximate the gate transition as a staircase and discretized in voltage as follows:

<table>
<thead>
<tr>
<th>Voltage</th>
<th>Discretized Gate Voltage</th>
</tr>
</thead>
<tbody>
<tr>
<td>$v_{in} + V_T$</td>
<td>$v_{GATE}$</td>
</tr>
<tr>
<td>$v_{in}$</td>
<td>$v_{CL}$</td>
</tr>
</tbody>
</table>

Slow Transition

Fast Transition

Charge injection due to fast transition

The time constant of the channel, $R_{channel}C_{channel}$, determines whether or not the capacitance, $C_L$, fully charges during each voltage step.

---

Analytical Expressions to Approximate Charge Injection/Clock Feedthrough

Assume the gate voltage is making a transition from high, $V_H$, to low, $V_L$.

$$v_{Gate} = v_G(t) = V_H - Ut$$

where $U$ = magnitude of the slope of $v_G(t)$

Define $V_{HT} = V_H - V_S - V_T$ and $\beta = \frac{K'W}{L}$.

The error in voltage across $C_L$, $V_{error}$, is given below in two terms. The first term corresponds to the feedthrough that occurs while the switch is still on and the second term corresponds to feedthrough when the switch is off.

1.) Slow transition occurs when $\frac{\beta V_{HT}}{2C_L} \gg U$.

$$V_{error} = -\left(\frac{W \cdot CGD0 + \frac{C_{channel}}{2}}{C_L}\right) \sqrt{\frac{\pi UC_L}{2\beta}} - \frac{W \cdot CGD0}{C_L} (V_S + 2V_T - V_L)$$

2.) Fast transition occurs when $\frac{\beta V_{HT}}{2C_L} \ll U$.

$$V_{error} = -\left(\frac{W \cdot CGD0 + \frac{C_{channel}}{2}}{C_L}\right) \left(V_{HT} - \frac{\beta V_{HT}^3}{6U \cdot C_L}\right) - \frac{W \cdot CGD0}{C_L} (V_S + 2V_T - V_L)$$
Example 2 - Calculation of Charge Feedthrough Error

Calculate the effect of charge feedthrough on the previous circuit where $V_S = 1\, \text{V}$, $C_L = 1\, \text{pF}$, $W/L = 0.8\mu\text{m}/0.8\mu\text{m}$, and $V_G$ is given below for the two cases. Use model parameters from Tables 3.1-2 and 3.2-1. Neglect $\Delta L$ and $\Delta W$ effects.

Solution

Case 1:

The value of $U$ is equal to $5\, \text{V}/0.2\, \text{nS}$ or $25\times10^9$. Next we must test to see if the slow or fast transition time is appropriate. First calculate the value of $V_T$ as

$$V_T = V_{T0} + \gamma \sqrt{2|\Phi|} - V_{BS} = 0.7 + 0.4\sqrt{0.7 + 1} - 0.4\sqrt{0.7} = 0.887\, \text{V}$$

Therefore,

$$V_{HT} = V_H - V_T = 5 - 1 - 0.887 = 3.113\, \text{V}$$

which corresponds to the fast transition case. Using the previous expression gives,

$$V_{error} = \frac{\beta V_{HT}^2}{2C_L} = \frac{110\times10^{-6} \times 3.113^2}{2 \times 1\, \text{pF}} = 5.32\times10^8 < 25\times10^9$$

Case 2:

In this case $U$ is equal to $5\, \text{V}/50\, \text{ns}$ or $1\times10^8$ which means that the slow transition case is valid ($1\times10^8 < 5.32\times10^8$).

Using the previous expression gives,

$$V_{error} = \frac{\sqrt{314\times10^{-6}}}{220\times10^{-6}} \times 176\times10^{-18} (1 + 1.774 - 0) = -3.39\, \text{mV}$$

Comment:

These results are not expected to give precise answers regarding the amount of charge feedthrough one should expect in an actual circuit. Rather, they are a guide to understand the effects of various circuit elements and terminal conditions in order to minimize unwanted behavior by design techniques.
Solutions to Charge Injection

1.) Use minimum size switches to reduce the overlap capacitances and/or increase $C_L$.
2.) Use a dummy compensating transistor.

![Fig. 4.1-19](image)

- Requires complementary clocks
- Complete cancellation is difficult and may in fact may make the feedthrough worse

3.) Use complementary switches (transmission gates)
4.) Use differential implementation of switched capacitor circuits (probably the best solution)

---

Input-Dependent Charge Injection

Examination of the error voltage reveals that,

$$\text{Error voltage} = \text{Component independent of input} + \text{Component dependent on input}$$

This only occurs for switches that are floating and is due to the fact that the input influences the voltage at which the transistor switches ($v_{in} \approx V_S = V_D$). Leads to spurious responses and other undesired results.

Solution:
Use delayed clocks to remove the input-dependence by removing the path for injection from the floating switches.

Assume that $C_s$ is charged to $V_{in}$ (both $\phi_1$ and $\phi_{1d}$ are high):

1.) $\phi_1$ opens, no input-dependent feedthrough because switch terminals (S3) are at ground potential.
2.) $\phi_{1d}$ opens, no feedthrough occurs because there is no current path (except through small parasitic capacitors).

![Fig. 4.1-20](image)
CMOS Switches (Transmission Gate)

Advantages:
• Feedthrough somewhat diminished
• Larger dynamic range
• Lower ON resistance

Disadvantages:
• Requires a complementary clock
• Requires more area

Example 3 - Charge Injection for a CMOS Switch

Calculate the effect of charge feedthrough on the circuit shown below. Assume that \( U = 5V/50ns = 10^8V/s \), \( v_{in} = 2.5V \) and ignore the bulk effect. Use the model parameters from Tables 3.1-2 and 3.2-1.

**Solution**

First we must identify the transition behavior. For the NMOS transistor we have

\[
\frac{\beta_N V_{HTN}}{2C_L} = \frac{110 \times 10^{-6} \cdot (5-2.5-0.7)^2}{2 \cdot 10^{-12}} = 1.78 \times 10^8
\]

For the PMOS transistor, noting that

\( V_{HTP} = V_S - |V_{TP}| - V_L = 2.5-0.7-0 = 1.8 \)

we have

\[
\frac{\beta_P V_{HTP}}{2C_L} = \frac{50 \times 10^{-6} \cdot (1.8)^2}{2 \cdot 10^{-12}} = 8.10 \times 10^7
\]

Thus, the NMOS transistor is in the slow transition and the PMOS transistor is in the fast transition regimes.
**Example 3 - Continued**

Error due to NMOS (slow transition):

\[
V_{\text{error}}(\text{NMOS}) = -\left(\frac{1.76 \times 10^{-18} + 0.5 \times 1.58 \times 10^{-15}}{10^{-12}}\right) \sqrt{\frac{\pi \times 10^{8} \times 10^{-12}}{2 \times 110 \times 10^{-6}}} - \frac{1.76 \times 10^{-18}}{10^{-12}} (2.5 + 1.4 - 0)
\]

\[= -1.840 \text{mV}\]

Error due to PMOS (fast transition):

\[
V_{\text{error}}(\text{PMOS}) = \left(\frac{1.76 \times 10^{-18} + 0.5 \times 1.58 \times 10^{-15}}{10^{-12}}\right) \left(1.8 \times \frac{50 \times 10^{-6} \times (1.8)^3}{6 \times 10^{8} \times 10^{-12}}\right) + \frac{1.76 \times 10^{-18}}{10^{-12}} (5 + 1.4 - 2.5)
\]

\[= 1.956 \text{mV}\]

Net error voltage due to charge injection is 116 μV. This will vary with \(V_S\).

---

**Dynamic Range of the CMOS Switch**

The switch dynamic range is the range of voltages at the switch terminals \((V_A = V_B = V_{A,B})\) over which the ON resistance is small.

![Spice File for CMOS Switch](image)

**Spice File:**

```
Simulation CMOS transmission switch resistance
M1 1 3 2 0 MNMOS L=1U W=10U
M2 1 0 2 3 MPMOS L=1U W=10U
.MODEL MNMOS NMOS VTO=0.7, KP=110U, +LAMBDA=0.04, GAMMA=0.4, PHI=0.7
.MODEL MPMOS PMOS VTO=-0.7, KP=50U, +LAMBDA=0.05, GAMMA=0.5, PHI=0.8
VDD 1 0
VAB 1 0
IA 2 0 DC 1U
.PROBE
.PLOT V(1,2)
.END
```

**Result:**

Low ON resistance over a wide voltage range is difficult as the power supply decreases.
Charge Pumps for Switches with Low Power Supply Voltages

As power supply voltages decrease below 2V, it becomes difficult to keep the switch on at a low value of on-resistance over the range of the power supply. The result is that \( r_{ON} \) becomes a function of the signal amplitude and produces harmonics. Consequently, charge pumps are used to provide a gate voltage above power supply.

Principle of a charge pump:

\[
v_{OUT} = 2V_{DD} \frac{C_2}{C_2 + C_L + C_{NMOSswitch}}
\]

Simulation of the Charge Pump Circuit†

Circuit:

Simulation:

**Bootstrapped Switches with High Reliability†**

In the previous charge pump switch driver, the amount of gate-source drive depends upon the input signal and can easily cause reliability problems because it becomes too large for low values of input signal.

The solution to this problem is a bootstrapped switch as shown.

Actual bootstrap switch:

ϕlow: M7 and M10 make $v_{g}=0$ and $C_3$ charges to $V_{DD}$. ϕ high: $C_3$ connected to $v_{GS11}$. M7 reduces the $v_{DS}$ and $v_{GS}$ of M10 when $\phi = 0$. M13 ensures that $v_{GS8} \leq V_{DD}$.

The parasitics at the source of M11 require this node to be driven from a low impedance.

---


CMOS Analog Circuit Design

© P.E. Allen - 201

---

**MOSFET DIODE**

**MOS Diode**

When the MOSFET has the gate connected to the drain, it acts like a diode with characteristics similar to a pn-junction diode.

![MOSFET_diode](fig4-21.png)

Note that when the gate is connected to the drain of an enhancement MOSFET, the MOSFET is always in the saturation region.

$v_{DS} \geq v_{GS} - V_{T} \Rightarrow v_{D} - v_{S} \geq v_{G} - v_{S} - V_{T} \Rightarrow v_{D} - v_{G} \geq -V_{T} \Rightarrow v_{DG} \geq -V_{T}$

Since $V_T$ is always greater than zero for an enhancement device, then $v_{DG} = 0$ satisfies the conditions for saturation.

- Works for NMOS or PMOS
- Note that the drain could be $V_T$ less than the gate and still be in saturation
How Does the MOS Diode Compare with a \textit{pn} Diode?

The comparison is basically the difference between an exponential and a square-law function. However, if the designer is willing to spend $W/L$, the comparison becomes more interesting as shown below.

If the threshold voltage is less than 0.4V, the MOS diode is a clear winner over the \textit{pn} junction diode even for modest $W/L$ ratios.

**SUMMARY**

- Symmetrical switching characteristics
- High OFF resistance
- Moderate ON resistance (OK for most applications)
- Clock feedthrough is proportional to size of switch ($W$) and inversely proportional to switching capacitors.
- Output offset due to clock feedthrough has 2 components:
  - Input dependent
  - Input independent
- Complementary switches help increase dynamic range.
- Fully differential operation should minimize the clock feedthrough.
- As power supply reduces, floating switches become more difficult to fully turn on.
- Switches contribute a $kT/C$ noise which can get folded back into the baseband.
- The gate-drain connected MOSFET can make a good diode realization.